JST2302H

20V,3A
N-Channel Mosfet

FEATURES

RDS(ON)≤ 46mΩ @VGS=4.5V

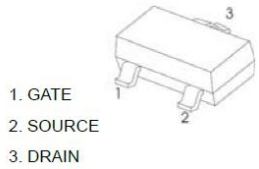
RDS(ON)≤ 70mΩ @VGS=2.5V

APPLICATIONS

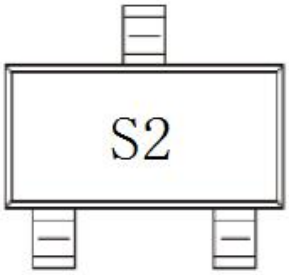
Load Switch for Portable Devices

DC/DC Converter

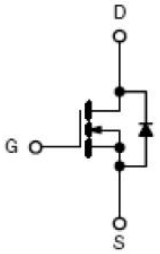
SOT-23



MARKING



N-CHANNEL MOSFET



Maximum ratings (T_a=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	±10	
Continuous Drain Current	I_D	3	A
Pulsed Drain Current	I_{DM}	12	
Maximum Power Dissipation	P_D	0.4	W
Thermal Resistance from Junction to Ambient(t ≤5s)	$R_{\theta JA}$	312	℃/W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{stg}	-55 ~+150	

MOSFET ELECTRICAL CHARACTERISTICS T_a=25 ℃ unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Static						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D =250μA	20	21		V
Gate-source threshold voltage	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =250μA	0.4	0.5	1.1	
Gate-source leakage	I_{GSS}	V_{DS} =0V, V_{GS} =±8V			±100	nA
Zero gate voltage drain current	I_{DSS}	V_{DS} =20V, V_{GS} =0V			1	μA
Drain-source on-state resistance [a]	$R_{DS(on)}$	V_{GS} =4.5V, I_D =4A		24	46	mΩ
		V_{GS} =2.5V, I_D =3.1A		31	70	
Forward transconductancea	g_{fs}	V_{DS}=5V， I_D=3.6A		9		S
Body diode voltage	V_{SD}	I_S=3A		0.8	1.3	V
Dynamic[b]						
Input capacitance	C_{iss}	V_{DS} =10V,V_{GS} =0V,f =1MHz		310		pF
Output capacitance	C_{oss}			125		
Reverse transfer capacitance	C_{rss}			86		
Total gate charge	Q_g	V_{DS} =10V,V_{GS} =4.5V,I_D =3.6A		4	10	nC
Gate-source charge	Q_{gs}			0.65		
Gate-drain charge	Q_{gd}			1.5		
Turn-on delay time	$t_{d(on)}$	V_{DD}=10V, R_L=5.5Ω, I_D =3.6A, V_{GEN}=4.5V,R_g=6Ω		8		ns
Rise time	t_r			57		
Turn-off delay time	$t_{d(off)}$			17		
Fall time	t_f			12		

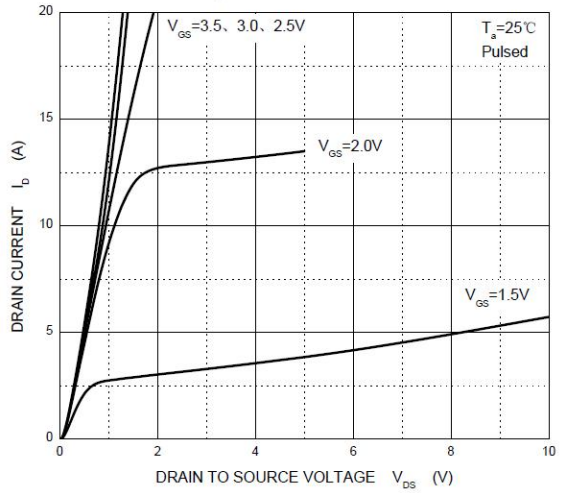
Notes :

a. Pulse Test : Pulse Width < 300μs, Duty Cycle ≤2%.

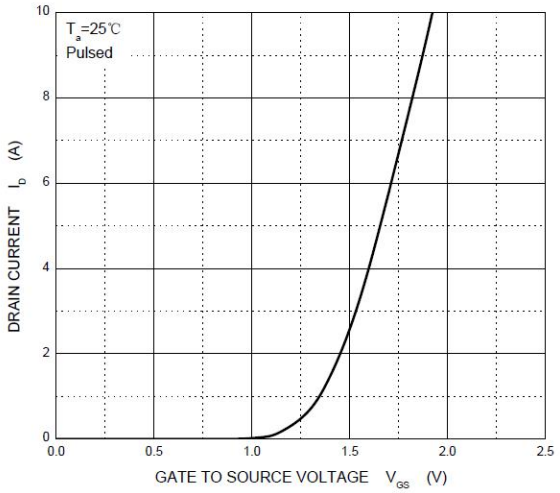
b. Guaranteed by design, not subject to production testing.

N-Channel 20V (D-S) MOSFET Typical Characteristics

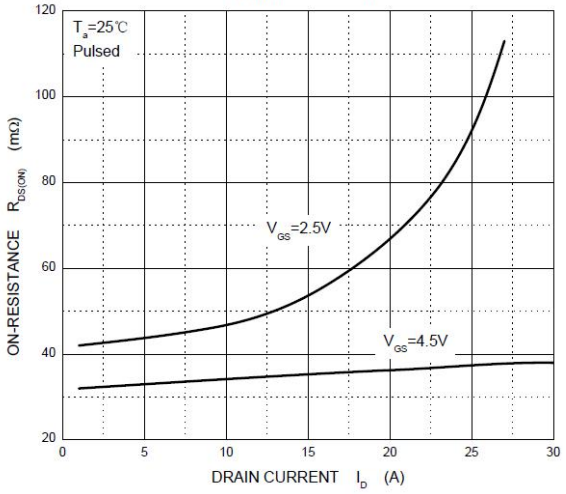
Output Characteristics



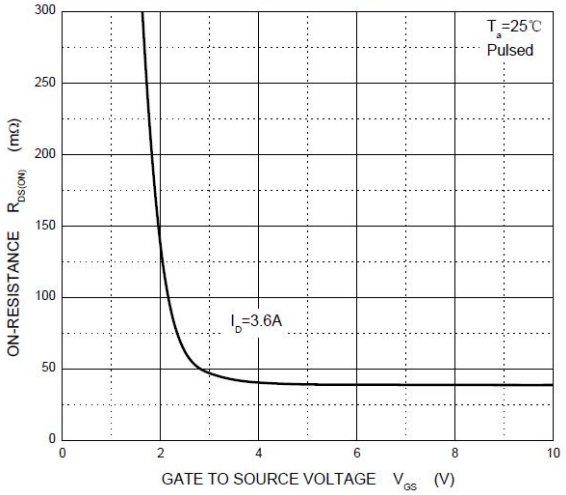
Transfer Characteristics



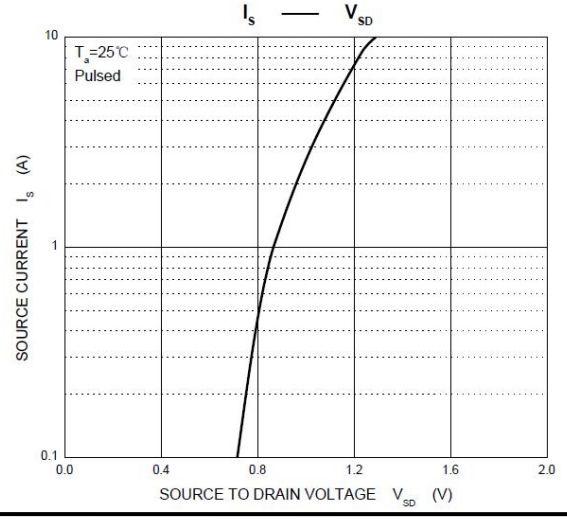
$R_{DS(ON)}$ — I_D



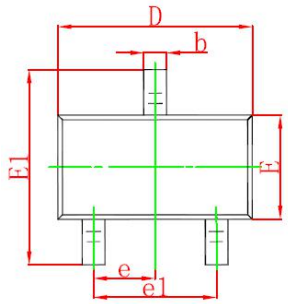
$R_{DS(ON)}$ — V_{GS}

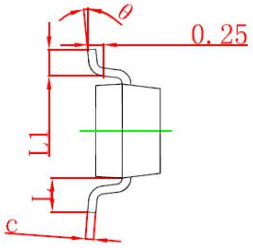


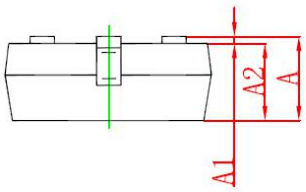
I_S — V_{SD}



SOT-23 package

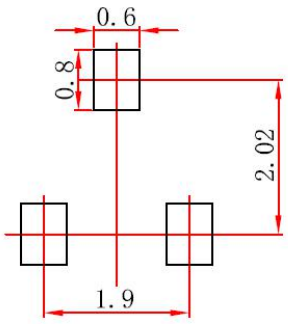






Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

SOT-23 Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.

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